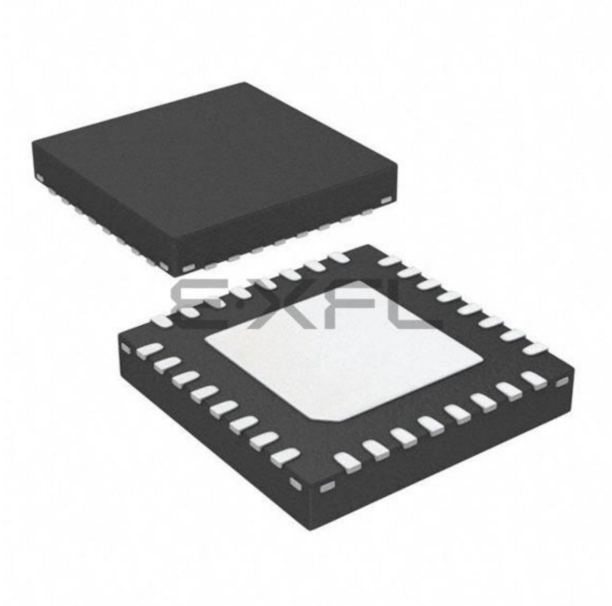

What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Discontinued at Digi-Key
Core Processor	CIP-51 8051
Core Size	8-Bit
Speed	72MHz
Connectivity	I²C, SMBus, SPI, UART/USART
Peripherals	Brown-out Detect/Reset, POR, PWM, WDT
Number of I/O	29
Program Memory Size	64KB (64K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	4.25K x 8
Voltage - Supply (Vcc/Vdd)	2.2V ~ 3.6V
Data Converters	A/D 20x14b; D/A 4x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 105°C (TA)
Mounting Type	Surface Mount
Package / Case	32-UFQFN Exposed Pad
Supplier Device Package	32-QFN (4x4)
Purchase URL	https://www.e-xfl.com/product-detail/silicon-labs/efm8lb12f64e-a-qfn32

2. Ordering Information

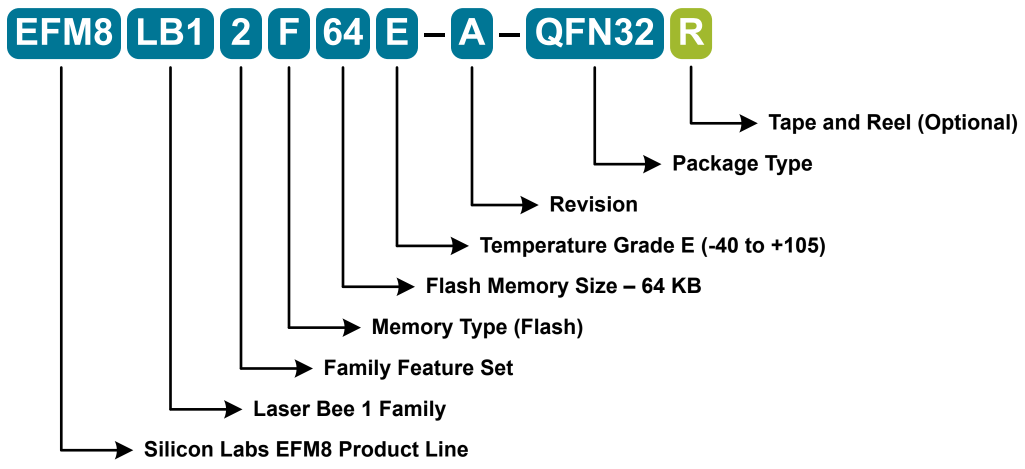

Figure 2.1. EFM8LB1 Part Numbering

All EFM8LB1 family members have the following features:

- CIP-51 Core running up to 72 MHz
- Three Internal Oscillators (72 MHz, 24.5 MHz and 80 kHz)
- SMBus
- I2C Slave
- SPI
- 2 UARTs
- 6-Channel Programmable Counter Array (PWM, Clock Generation, Capture/Compare)
- Six 16-bit Timers
- Four Configurable Logic Units
- 14-bit Analog-to-Digital Converter with integrated multiplexer, voltage reference, temperature sensor, channel sequencer, and direct-to-XRAM data transfer
- Two Analog Comparators
- 16-bit CRC Unit
- AEC-Q100 qualified (pending)

In addition to these features, each part number in the EFM8LB1 family has a set of features that vary across the product line. The product selection guide shows the features available on each family member.

Table 2.1. Product Selection Guide

Ordering Part Number	Flash Memory (kB)	RAM (Bytes)	Digital Port I/Os (Total)	ADC0 Channels	Voltage DACs	Comparator 0 Inputs	Comparator 1 Inputs	Pb-free (RoHS Compliant)	Temperature Range	Package
EFM8LB12F64E-A-QFN32	64	4352	29	20	4	10	9	Yes	-40 to +105 °C	QFN32
EFM8LB12F64E-A-QFP32	64	4352	28	20	4	10	9	Yes	-40 to +105 °C	QFP32
EFM8LB12F64E-A-QFN24	64	4352	20	12	4	6	6	Yes	-40 to +105 °C	QFN24
EFM8LB12F64E-A-QSOP24	64	4352	21	13	4	6	7	Yes	-40 to +105 °C	QSOP24

Ordering Part Number	Flash Memory (kB)	RAM (Bytes)	Digital Port I/Os (Total)	ADC0 Channels	Voltage DACs	Comparator 0 Inputs	Comparator 1 Inputs	Pb-free (RoHS Compliant)	Temperature Range	Package
EFM8LB12F32E-A-QFN32	32	2304	29	20	4	10	9	Yes	-40 to +105 °C	QFN32
EFM8LB12F32E-A-QFP32	32	2304	28	20	4	10	9	Yes	-40 to +105 °C	QFP32
EFM8LB12F32E-A-QFN24	32	2304	20	12	4	6	6	Yes	-40 to +105 °C	QFN24
EFM8LB12F32E-A-QSOP24	32	2304	21	13	4	6	7	Yes	-40 to +105 °C	QSOP24
EFM8LB11F32E-A-QFN32	32	2304	29	20	2	10	9	Yes	-40 to +105 °C	QFN32
EFM8LB11F32E-A-QFP32	32	2304	28	20	2	10	9	Yes	-40 to +105 °C	QFP32
EFM8LB11F32E-A-QFN24	32	2304	20	12	2	6	6	Yes	-40 to +105 °C	QFN24
EFM8LB11F32E-A-QSOP24	32	2304	21	13	2	6	7	Yes	-40 to +105 °C	QSOP24
EFM8LB11F16E-A-QFN32	16	1280	29	20	2	10	9	Yes	-40 to +105 °C	QFN32
EFM8LB11F16E-A-QFP32	16	1280	28	20	2	10	9	Yes	-40 to +105 °C	QFP32
EFM8LB11F16E-A-QFN24	16	1280	20	12	2	6	6	Yes	-40 to +105 °C	QFN24
EFM8LB11F16E-A-QSOP24	16	1280	21	13	2	6	7	Yes	-40 to +105 °C	QSOP24
EFM8LB10F16E-A-QFN32	16	1280	29	20	0	10	9	Yes	-40 to +105 °C	QFN32
EFM8LB10F16E-A-QFP32	16	1280	28	20	0	10	9	Yes	-40 to +105 °C	QFP32
EFM8LB10F16E-A-QFN24	16	1280	20	12	0	6	6	Yes	-40 to +105 °C	QFN24
EFM8LB10F16E-A-QSOP24	16	1280	21	13	0	6	7	Yes	-40 to +105 °C	QSOP24

3. System Overview

3.1 Introduction

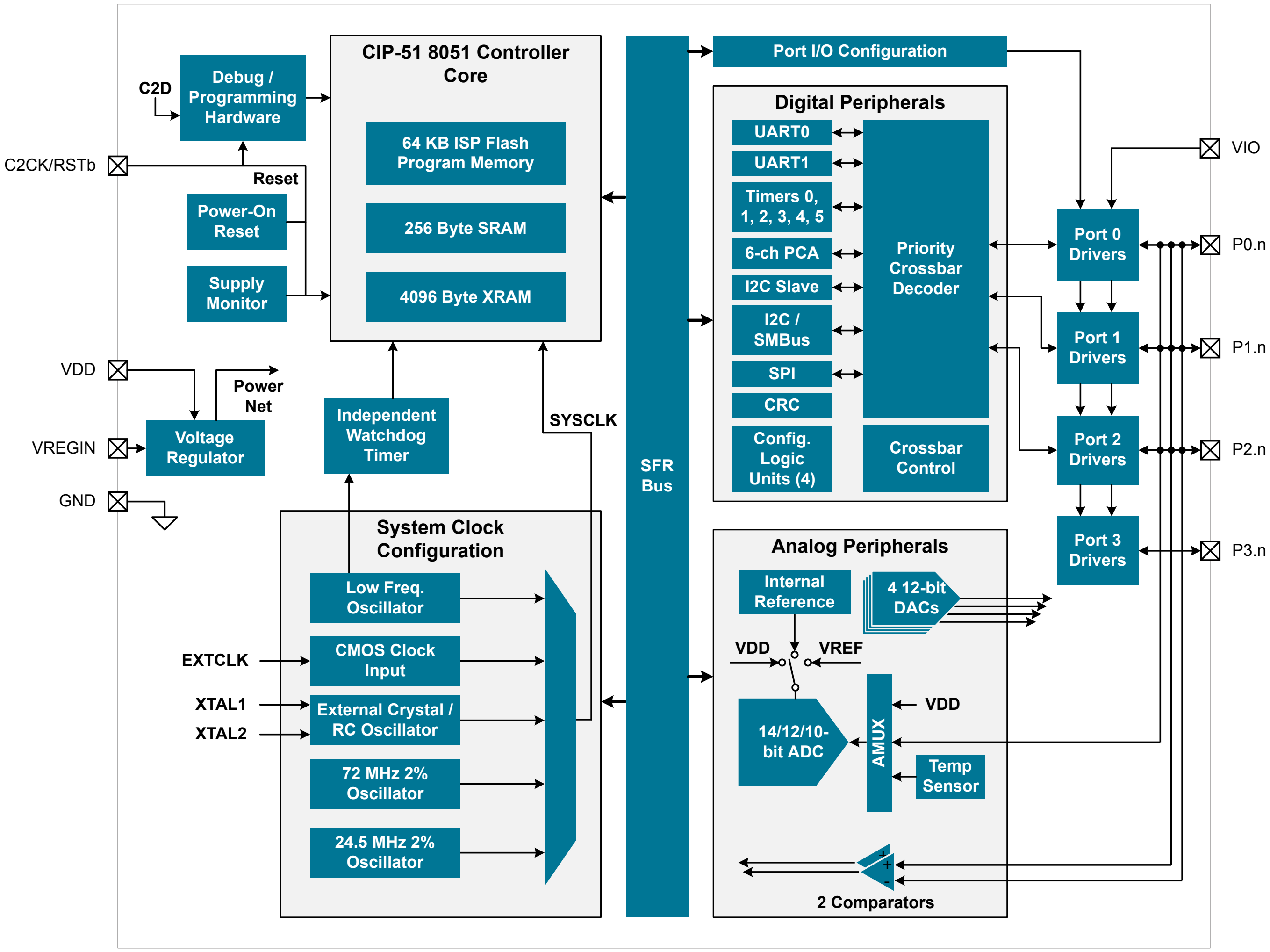

Figure 3.1. Detailed EFM8LB1 Block Diagram

4.1.4 Flash Memory

Table 4.4. Flash Memory

Parameter	Symbol	Test Condition	Min	Typ	Max	Units
Write Time[1, 2]	t_{WRITE}	One Byte, F_{SYSCLK} = 24.5 MHz	19	20	21	µs
Erase Time[1, 2]	t_{ERASE}	One Page, F_{SYSCLK} = 24.5 MHz	5.2	5.35	5.5	ms
V_{DD} Voltage During Programming[3]	V_{PROG}		2.2	—	3.6	V
Endurance (Write/Erase Cycles)	N_{WE}		20k	100k	—	Cycles

Note:

1. Does not include sequencing time before and after the write/erase operation, which may be multiple SYSCLK cycles.
2. The internal High-Frequency Oscillator 0 has a programmable output frequency, which is factory programmed to 24.5 MHz. If user firmware adjusts the oscillator speed, it must be between 22 and 25 MHz during any flash write or erase operation. It is recommended to write the HFO0CAL register back to its reset value when writing or erasing flash.
3. Flash can be safely programmed at any voltage above the supply monitor threshold (V_{VDDM}).
4. Data Retention Information is published in the Quarterly Quality and Reliability Report.

4.1.5 Power Management Timing

Table 4.5. Power Management Timing

Parameter	Symbol	Test Condition	Min	Typ	Max	Units
Idle Mode Wake-up Time	t_{IDLEWK}		2	—	3	SYSCLKs
Suspend Mode Wake-up Time	$t_{SUSPENDWK}$	SYSCLK = HFOSC0 CLKDIV = 0x00	—	170	—	ns
Snooze Mode Wake-up Time	$t_{SLEEPWK}$	SYSCLK = HFOSC0 CLKDIV = 0x00	—	12	—	µs

4.1.8 Crystal Oscillator

Table 4.8. Crystal Oscillator

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Crystal Frequency	f_{XTAL}		0.02	—	25	MHz
Crystal Drive Current	I_{XTAL}	XFCN = 0	—	0.5	—	µA
		XFCN = 1	—	1.5	—	µA
		XFCN = 2	—	4.8	—	µA
		XFCN = 3	—	14	—	µA
		XFCN = 4	—	40	—	µA
		XFCN = 5	—	120	—	µA
		XFCN = 6	—	550	—	µA
		XFCN = 7	—	2.6	—	mA

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Power Supply Rejection Ratio	$PSRR_{ADC}$		—	TBD	—	dB
DC Performance						
Integral Nonlinearity	INL	14 Bit Mode	—	TBD	—	LSB
		12 Bit Mode	-1.4	TBD	+1.4	LSB
		10 Bit Mode	—	TBD	—	LSB
Differential Nonlinearity (Guaranteed Monotonic)	DNL	14 Bit Mode	—	TBD	—	LSB
		12 Bit Mode	—	TBD	0.9	LSB
		10 Bit Mode	—	TBD	—	LSB
Offset Error	E_{OFF}	14 Bit Mode	—	TBD	—	LSB
		12 Bit Mode	-2	TBD	2	LSB
		10 Bit Mode	—	TBD	—	LSB
Offset Temperature Coefficient	TC_{OFF}		—	TBD	—	LSB/°C
Slope Error	E_M	14 Bit Mode	—	TBD	—	%
		12 Bit Mode	—	TBD	TBD	%
		10 Bit Mode	—	TBD	—	%
Dynamic Performance 10 kHz Sine Wave Input 1 dB below full scale, Max throughput, using AGND pin						
Signal-to-Noise	SNR	14 Bit Mode	—	TBD	—	dB
		12 Bit Mode	TBD	TBD	—	dB
		10 Bit Mode	—	TBD	—	dB
Signal-to-Noise Plus Distortion	SNDR	14 Bit Mode	—	TBD	—	dB
		12 Bit Mode	TBD	TBD	—	dB
		10 Bit Mode	—	TBD	—	dB
Total Harmonic Distortion (Up to 5th Harmonic)	THD	14 Bit Mode	—	TBD	—	dB
		12 Bit Mode	—	TBD	—	dB
		10 Bit Mode	—	TBD	—	dB
Spurious-Free Dynamic Range	SFDR	14 Bit Mode	—	TBD	—	dB
		12 Bit Mode	—	TBD	—	dB
		10 Bit Mode	—	TBD	—	dB

Note:

1. This time is equivalent to four periods of a clock running at 18 MHz + 2%.
2. Conversion Time does not include Tracking Time. Total Conversion Time is:

   Total Conversion Time = [RPT × (ADTK + NUMBITS + 1) × T(SARCLK)] + (T(ADCCLK) × 4)

   where RPT is the number of conversions represented by the ADRPT field and ADCCLK is the clock selected for the ADC.
3. Absolute input pin voltage is limited by the V_{IO} supply.

4.1.10 Voltage Reference

Table 4.10. Voltage Reference

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Internal Fast Settling Reference						
Output Voltage (Full Temperature and Supply Range)	V_{REFFS}		1.62	1.65	1.68	V
Temperature Coefficient	TC_{REFFS}		—	50	—	ppm/°C
Turn-on Time	t_{REFFS}		—	—	1.5	µs
Power Supply Rejection	$PSRR_{REFFS}$		—	400	—	ppm/V
On-chip Precision Reference						
Valid Supply Range	V_{DD}	1.2 V Output	2.2	—	3.6	V
		2.4 V Output	2.7	—	3.6	V
Output Voltage	V_{REFP}	1.2 V Output, T = 25 °C	TBD	1.2	TBD	V
		2.4 V Output, T = 25 °C	TBD	2.4	TBD	V
Turn-on Time, settling to 0.5 LSB	t_{VREFP}	4.7 µF tantalum + 0.1 µF ceramic bypass on VREF pin	—	3	—	ms
		0.1 µF ceramic bypass on VREF pin	—	100	—	µs
Load Regulation	LR_{VREFP}	Load = 0 to 200 µA to GND	—	TBD	—	µV/µA
Load Capacitor	C_{VREFP}	Load = 0 to 200 µA to GND	0.1	—	—	µF
Short-circuit current	ISC_{VREFP}		—	—	8	mA
Power Supply Rejection	$PSRR_{VREFP}$		—	TBD	—	ppm/V
External Reference						
Input Current	I_{EXTREF}	ADC Sample Rate = 1 Msps; VREF = 3.0 V	—	5	—	µA

4.1.12 DACs

Table 4.12. DACs

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Resolution	N_{bits}			12		Bits
Throughput Rate	f_S		—	—	200	ksps
Integral Nonlinearity	INL		TBD	±0.5	TBD	LSB
Differential Nonlinearity	DNL		TBD	±5	TBD	LSB
Output Noise	VREF = 2.4 V f_S = 0.1 Hz to 300 kHz		—	110	—	μV_{RMS}
Slew Rate	SLEW		—	±1	—	V/µs
Output Settling Time to 1 LSB	t_{SETTLE}	V_{OUT} change between 25% and 75% Full Scale	—	2.6	5	µs
Power-on Time	t_{PWR}		—	—	10	µs
Voltage Reference Range	V_{REF}		1.15	—	V_{DD}	V
Power Supply Rejection Ratio	PSRR	DC, V_{OUT} = 50% Full Scale	—	110	—	dB
		1 kHz, V_{OUT} = 50% Full Scale	—	60	—	dB
Total Harmonic Distortion	THD	V_{OUT} = 10 kHz sine wave, 10% to 90%	60	—	—	dB
Offset Error	E_{OFF}	VREF = 2.4 V	TBD	±0.5	TBD	LSB
Offset Temperature Coefficient	TC_{OFF}		—	TBD	—	ppm/°C
Full-Scale Error	E_{FS}	VREF = 2.4 V	TBD	±5	TBD	LSB
Full-Scale Error Tempco	TC_{FS}		—	TBD	—	ppm/°C
External Load Impedance	R_{LOAD}		2	—	—	kΩ
External Load Capacitance	C_{LOAD}		TBD	—	100	pF
Load Regulation		V_{OUT} = 50% Full Scale I_{OUT} = -2 to 2 mA	—	100	TBD	µV/mA

4.1.13 Comparators

Table 4.13. Comparators

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Response Time, CPMD = 00 (Highest Speed)	t_{RESP0}	+100 mV Differential	—	100	—	ns
		-100 mV Differential	—	150	—	ns
Response Time, CPMD = 11 (Lowest Power)	t_{RESP3}	+100 mV Differential	—	1.5	—	µs
		-100 mV Differential	—	3.5	—	µs
Positive Hysteresis Mode 0 (CPMD = 00)	HYS_{CP+}	CPHYP = 00	—	0.4	—	mV
		CPHYP = 01	—	8	—	mV
		CPHYP = 10	—	16	—	mV
		CPHYP = 11	—	32	—	mV
Negative Hysteresis Mode 0 (CPMD = 00)	HYS_{CP-}	CPHYN = 00	—	-0.4	—	mV
		CPHYN = 01	—	-8	—	mV
		CPHYN = 10	—	-16	—	mV
		CPHYN = 11	—	-32	—	mV
Positive Hysteresis Mode 1 (CPMD = 01)	HYS_{CP+}	CPHYP = 00	—	0.5	—	mV
		CPHYP = 01	—	6	—	mV
		CPHYP = 10	—	12	—	mV
		CPHYP = 11	—	24	—	mV
Negative Hysteresis Mode 1 (CPMD = 01)	HYS_{CP-}	CPHYN = 00	—	-0.5	—	mV
		CPHYN = 01	—	-6	—	mV
		CPHYN = 10	—	-12	—	mV
		CPHYN = 11	—	-24	—	mV
Positive Hysteresis Mode 2 (CPMD = 10)	HYS_{CP+}	CPHYP = 00	—	0.7	—	mV
		CPHYP = 01	—	4.5	—	mV
		CPHYP = 10	—	9	—	mV
		CPHYP = 11	—	18	—	mV
Negative Hysteresis Mode 2 (CPMD = 10)	HYS_{CP-}	CPHYN = 00	—	-0.6	—	mV
		CPHYN = 01	—	-4.5	—	mV
		CPHYN = 10	—	-9	—	mV
		CPHYN = 11	—	-18	—	mV
Positive Hysteresis Mode 3 (CPMD = 11)	HYS_{CP+}	CPHYP = 00	—	1.5	—	mV
		CPHYP = 01	—	4	—	mV
		CPHYP = 10	—	8	—	mV
		CPHYP = 11	—	16	—	mV

4.2 Thermal Conditions

Table 4.16. Thermal Conditions

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Thermal Resistance	θ_{JA}	QFN24 Packages	—	TBD	—	°C/W
		QFN32 Packages	—	TBD	—	°C/W
		QFP32 Packages	—	80	—	°C/W
		QSOP24 Packages	—	65	—	°C/W

Note:

1. Thermal resistance assumes a multi-layer PCB with any exposed pad soldered to a PCB pad.

4.3 Absolute Maximum Ratings

Stresses above those listed in Table 4.17 Absolute Maximum Ratings on page 27 may cause permanent damage to the device. This is a stress rating only and functional operation of the devices at those or any other conditions above those indicated in the operation listings of this specification is not implied. Exposure to maximum rating conditions for extended periods may affect device reliability. For more information on the available quality and reliability data, see the Quality and Reliability Monitor Report at http://www.silabs.com/support/quality/pages/default.aspx.

Table 4.17. Absolute Maximum Ratings

Parameter	Symbol	Test Condition	Min	Max	Unit
Ambient Temperature Under Bias	T_{BIAS}		-55	125	°C
Storage Temperature	T_{STG}		-65	150	°C
Voltage on VDD	V_{DD}		GND-0.3	4.2	V
Voltage on VIO[2]	V_{IO}		GND-0.3	V_{DD}+0.3	V
Voltage on I/O pins or RSTb, excluding P2.0-P2.3 (QFN24 and QSOP24) or P3.0-P3.3 (QFN32 and QFP32)	V_{IN}	V_{IO} > TBD V	GND-0.3	TBD	V
		V_{IO} < TBD V	GND-0.3	TBD	V
Voltage on P2.0-P2.3 (QFN24 and QSOP24) or P3.0-P3.3 (QFN32 and QFP32)	V_{IN}		GND-0.3	V_{DD}+0.3	V
Total Current Sunk into Supply Pin	I_{VDD}		—	400	mA
Total Current Sourced out of Ground Pin	I_{GND}		400	—	mA
Current Sourced or Sunk by any I/O Pin or RSTb	I_{IO}		-100	100	mA

Note:

1. Exposure to maximum rating conditions for extended periods may affect device reliability.
2. In certain package configurations, the VIO and VDD supplies are bonded to the same pin.

Pin Number	Pin Name	Description	Crossbar Capability	Additional Digital Functions	Analog Functions
15	P2.2	Multifunction I/O	Yes	P2MAT.2 CLU2OUT CLU1A.15 CLU2B.14 CLU3A.14	ADC0.15 CMP1P.4 CMP1N.4
16	P2.1	Multifunction I/O	Yes	P2MAT.1 I2C0_SCL CLU1B.14 CLU2A.15 CLU3B.15	ADC0.14 CMP1P.3 CMP1N.3
17	P2.0	Multifunction I/O	Yes	P2MAT.0 I2C0_SDA CLU1A.14 CLU2A.14 CLU3B.14	CMP1P.2 CMP1N.2
18	P1.7	Multifunction I/O	Yes	P1MAT.7 CLU0B.15 CLU1B.13 CLU2A.13	ADC0.13 CMP0P.9 CMP0N.9
19	P1.6	Multifunction I/O	Yes	P1MAT.6 CLU0A.15 CLU1B.12 CLU2A.12	ADC0.12
20	P1.5	Multifunction I/O	Yes	P1MAT.5 CLU0B.14 CLU1A.13 CLU2B.13 CLU3B.11	ADC0.11
21	P1.4	Multifunction I/O	Yes	P1MAT.4 CLU0A.14 CLU1A.12 CLU2B.12 CLU3B.10	ADC0.10

Pin Number	Pin Name	Description	Crossbar Capability	Additional Digital Functions	Analog Functions
18	P1.7	Multifunction I/O	Yes	P1MAT.7 CLU0B.15 CLU1B.13 CLU2A.13	ADC0.13 CMP0P.9 CMP0N.9
19	P1.6	Multifunction I/O	Yes	P1MAT.6 CLU0A.15 CLU1B.12 CLU2A.12	ADC0.12
20	P1.5	Multifunction I/O	Yes	P1MAT.5 CLU0B.14 CLU1A.13 CLU2B.13 CLU3B.11	ADC0.11
21	P1.4	Multifunction I/O	Yes	P1MAT.4 CLU0A.14 CLU1A.12 CLU2B.12 CLU3B.10	ADC0.10
22	P1.3	Multifunction I/O	Yes	P1MAT.3 CLU0B.13 CLU1B.11 CLU2B.11 CLU3A.13	ADC0.9
23	P1.2	Multifunction I/O	Yes	P1MAT.2 CLU0A.13 CLU1A.11 CLU2B.10 CLU3A.12 CLU3B.13	ADC0.8 CMP0P.8 CMP0N.8
24	P1.1	Multifunction I/O	Yes	P1MAT.1 CLU0B.12 CLU1B.10 CLU2A.11 CLU3B.12	ADC0.7 CMP0P.7 CMP0N.7

Pin Number	Pin Name	Description	Crossbar Capability	Additional Digital Functions	Analog Functions
25	P1.0	Multifunction I/O	Yes	P1MAT.0 CLU1OUT CLU0A.12 CLU1A.10 CLU2A.10	ADC0.6 CMP0P.6 CMP0N.6 CMP1P.1 CMP1N.1
26	P0.7	Multifunction I/O	Yes	P0MAT.7 INT0.7 INT1.7 CLU0B.11 CLU1B.9 CLU3A.11	ADC0.5 CMP0P.5 CMP0N.5 CMP1P.0 CMP1N.0
27	P0.6	Multifunction I/O	Yes	P0MAT.6 CNVSTR INT0.6 INT1.6 CLU0A.11 CLU1B.8 CLU3A.10	ADC0.4 CMP0P.4 CMP0N.4
28	P0.5	Multifunction I/O	Yes	P0MAT.5 INT0.5 INT1.5 UART0_RX CLU0B.10 CLU1A.9	ADC0.3 CMP0P.3 CMP0N.3
29	P0.4	Multifunction I/O	Yes	P0MAT.4 INT0.4 INT1.4 UART0_TX CLU0A.10 CLU1A.8	ADC0.2 CMP0P.2 CMP0N.2

6.3 EFM8LB1x-QFN24 Pin Definitions

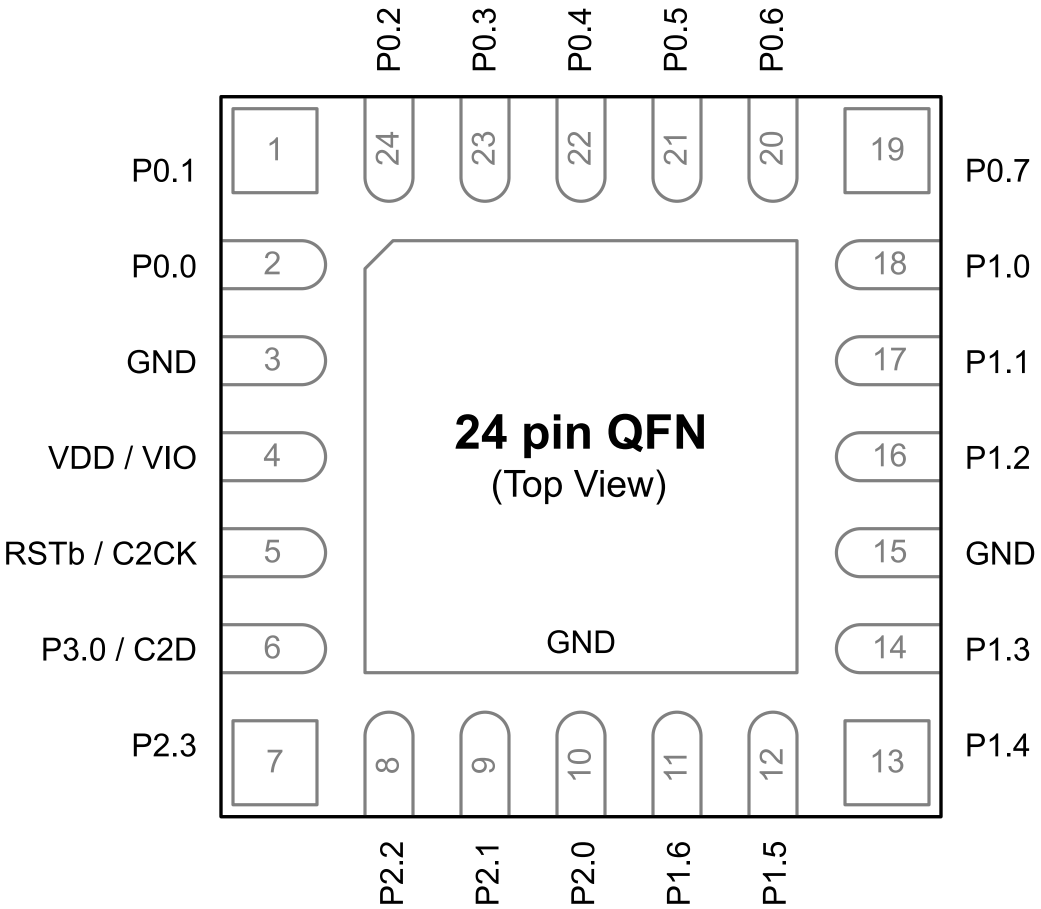

Figure 6.3. EFM8LB1x-QFN24 Pinout

Table 6.3. Pin Definitions for EFM8LB1x-QFN24

Pin Number	Pin Name	Description	Crossbar Capability	Additional Digital Functions	Analog Functions
1	P0.1	Multifunction I/O	Yes	P0MAT.1 INT0.1 INT1.1 CLU0B.8 CLU2A.9 CLU3B.9	ADC0.0 CMP0P.0 CMP0N.0 AGND

Pin Number	Pin Name	Description	Crossbar Capability	Additional Digital Functions	Analog Functions
2	P0.2	Multifunction I/O	Yes	P0MAT.2 INT0.2 INT1.2 CLU0OUT CLU0A.9 CLU2B.8 CLU3A.8	XTAL1 ADC0.1 CMP0P.1 CMP0N.1
3	P0.1	Multifunction I/O	Yes	P0MAT.1 INT0.1 INT1.1 CLU0B.8 CLU2A.9 CLU3B.9	ADC0.0 CMP0P.0 CMP0N.0 AGND
4	P0.0	Multifunction I/O	Yes	P0MAT.0 INT0.0 INT1.0 CLU0A.8 CLU2A.8 CLU3B.8	VREF
5	GND	Ground			
6	VDD / VIO	Supply Power Input			
7	RSTb / C2CK	Active-low Reset / C2 Debug Clock			
8	P3.0 / C2D	Multifunction I/O / C2 Debug Data			
9	P2.3	Multifunction I/O	Yes	P2MAT.3 CLU1B.15 CLU2B.15 CLU3A.15	DAC3
10	P2.2	Multifunction I/O	Yes	P2MAT.2 CLU1A.15 CLU2B.14 CLU3A.14	DAC2

Pin Number	Pin Name	Description	Crossbar Capability	Additional Digital Functions	Analog Functions
24	P0.4	Multifunction I/O	Yes	P0MAT.4 INT0.4 INT1.4 UART0_TX CLU0A.10 CLU1A.8	ADC0.2 CMP0P.2 CMP0N.2

Dimension	Min	Max
Note: 1. All dimensions shown are in millimeters (mm) unless otherwise noted. 2. Dimensioning and Tolerancing is per the ANSI Y14.5M-1994 specification. 3. This Land Pattern Design is based on the IPC-7351 guidelines. 4. All dimensions shown are at Maximum Material Condition (MMC). Least Material Condition (LMC) is calculated based on a Fabrication Allowance of 0.05mm. 5. All metal pads are to be non-solder mask defined (NSMD). Clearance between the solder mask and the metal pad is to be 60 µm minimum, all the way around the pad. 6. A stainless steel, laser-cut and electro-polished stencil with trapezoidal walls should be used to assure good solder paste release. 7. The stencil thickness should be 0.125 mm (5 mils). 8. The ratio of stencil aperture to land pad size should be 1:1 for all perimeter pads. 9. A 2 x 2 array of 1.10 mm square openings on a 1.30 mm pitch should be used for the center pad. 10. A No-Clean, Type-3 solder paste is recommended. 11. The recommended card reflow profile is per the JEDEC/IPC J-STD-020 specification for Small Body Components.		

7.3 QFN32 Package Marking

Figure 7.3. QFN32 Package Marking

The package marking consists of:

- PPPPPPPP – The part number designation.
- TTTTTT – A trace or manufacturing code.
- YY – The last 2 digits of the assembly year.
- WW – The 2-digit workweek when the device was assembled.
- # – The device revision (A, B, etc.).

8.3 QFP32 Package Marking

Figure 8.3. QFP32 Package Marking

The package marking consists of:

- PPPPPPPP – The part number designation.
- TTTTTT – A trace or manufacturing code.
- YY – The last 2 digits of the assembly year.
- WW – The 2-digit workweek when the device was assembled.
- # – The device revision (A, B, etc.).

10. QSOP24 Package Specifications

10.1 QSOP24 Package Dimensions

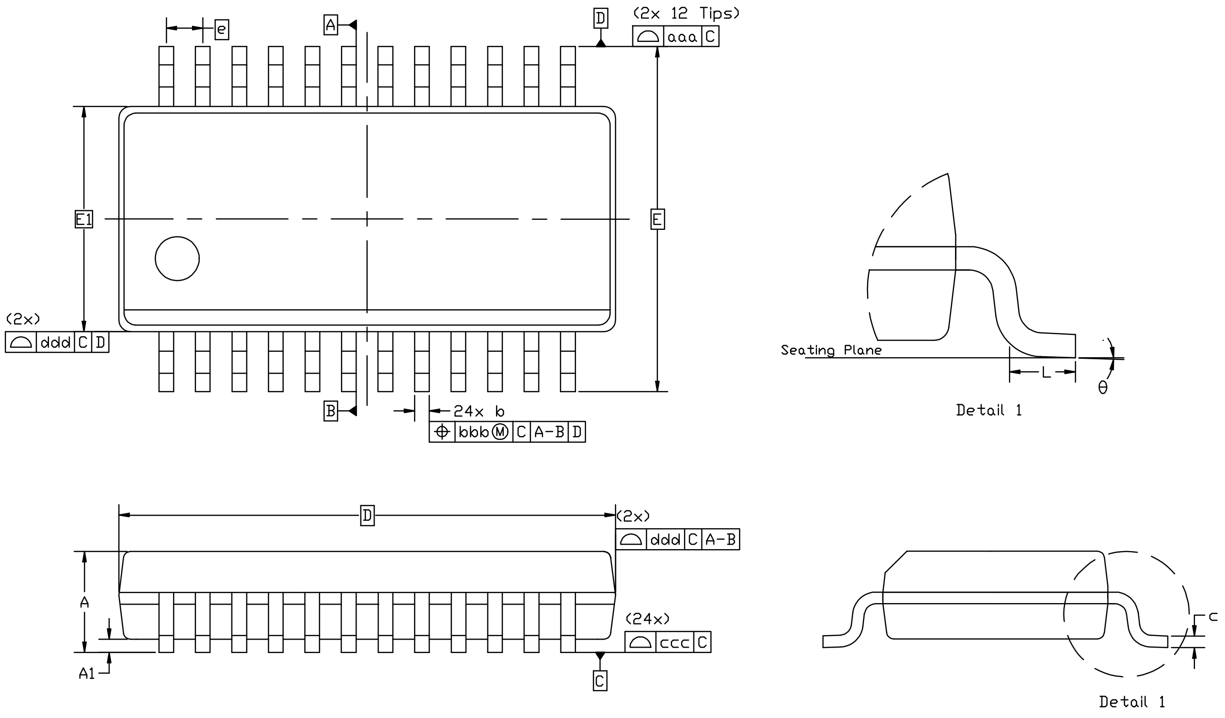

Figure 10.1. QSOP24 Package Drawing

Table 10.1. QSOP24 Package Dimensions

Dimension	Min	Typ	Max
A	—	—	1.75
A1	0.10	—	0.25
b	0.20	—	0.30
c	0.10	—	0.25
D	8.65 BSC		
E	6.00 BSC		
E1	3.90 BSC		
e	0.635 BSC		
L	0.40	—	1.27
theta	0º	—	8º

11. Revision History

11.1 Revision 0.1

Initial release.

11.2 Revision 0.2

Added information on the bootloader to 3.10 Bootloader.

Updated some characterization TBD values.